













CSD18513Q5A

SLPS623A - NOVEMBER 2016-REVISED JANUARY 2017

CSD18513Q5A 40-V N-Channel NexFET™ Power MOSFET

Features

- Low R_{DS(ON)}
- Low-Thermal Resistance
- Avalanche Rated
- Logic Level
- Lead-Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

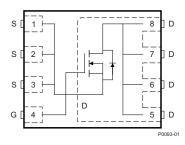
Applications

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- **Battery Motor Control**

3 Description

This 40-V, 2.8-mΩ, 5-mm × 6-mm SON NexFET™ power MOSFET is designed to minimize losses in power conversion applications.





R_{DS(on)} vs V_{GS} T_C = 25℃, I_D = 19 A R_{DS(on)} - On-State Resistance (mΩ) $T_C = 125$ °C, $I_D = 19$ A 10 2 0 0 10 12 20 V_{GS} - Gate-to-Source Voltage (V)

Product Summary

| $T_A = 25^\circ$ | С | TYPICAL VA | UNIT | |
|---------------------|-------------------------------|-----------------------------|------|-------|
| V_{DS} | Drain-to-Source Voltage 40 | | | ٧ |
| Q_g | Gate Charge Total (10 V) | 45 | | nC |
| Q_{gd} | Gate Charge Gate-to-Drain | 8.8 | | nC |
| D | Drain-to-Source On Resistance | V _{GS} = 4.5 V 4.1 | | mΩ |
| R _{DS(on)} | Drain-to-Source On Resistance | V _{GS} = 10 V 2.8 | | 11177 |
| V _{GS(th)} | Threshold Voltage | 1.8 | | V |

Device Information⁽¹⁾

| DEVICE | MEDIA | QTY | PACKAGE | SHIP |
|--------------|--------------|------|--------------------------------------|-------------|
| CSD18513Q5A | 13-Inch Reel | 2500 | SON | Tape |
| CSD18513Q5AT | 7-Inch Reel | 250 | 5.00-mm × 6.00-mm Plastic Package | and Reel |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

| Absolute Maximum Ratings | | | | | | |
|--|---|--|--|--|--|--|
| 5°C | VALUE | UNIT | | | | |
| Drain-to-Source Voltage | 40 | V | | | | |
| Gate-to-Source Voltage | ±20 | V | | | | |
| Continuous Drain Current (Package Limited) | 100 | | | | | |
| Continuous Drain Current (Silicon Limited), T _C = 25°C | 124 | Α | | | | |
| Continuous Drain Current ⁽¹⁾ | 22 | | | | | |
| Pulsed Drain Current ⁽²⁾ | 400 | Α | | | | |
| Power Dissipation ⁽¹⁾ | 3.1 | 101 | | | | |
| Power Dissipation, T _C = 25°C | 96 | W | | | | |
| Operating Junction, Storage Temperature | -55 to 150 | °C | | | | |
| Avalanche Energy, Single Pulse I _D = 46 A, L = 0.1 mH, R _G = 25 Ω | 106 | mJ | | | | |
| | Drain-to-Source Voltage Gate-to-Source Voltage Continuous Drain Current (Package Limited) Continuous Drain Current (Silicon Limited), T _C = 25°C Continuous Drain Current ⁽¹⁾ Pulsed Drain Current ⁽²⁾ Power Dissipation ⁽¹⁾ Power Dissipation, T _C = 25°C Operating Junction, Storage Temperature Avalanche Energy, Single Pulse | Drain-to-Source Voltage Drain-to-Source Voltage Gate-to-Source Voltage Continuous Drain Current (Package Limited) Continuous Drain Current (Silicon Limited), T _C = 25°C Continuous Drain Current ⁽¹⁾ Pulsed Drain Current ⁽²⁾ Power Dissipation ⁽¹⁾ Power Dissipation, T _C = 25°C Operating Junction, Storage Temperature Avalanche Energy, Single Pulse | | | | |

- (1) Typical $R_{\theta JA} = 40^{\circ}\text{C/W}$ on a 1-in², 2-oz Cu pad on a 0.06-in thick FR4 PCB.
- (2) Max $R_{\theta,JC} = 1.3$ °C/W, pulse duration $\leq 100 \mu s$, duty cycle \leq

Gate Charge

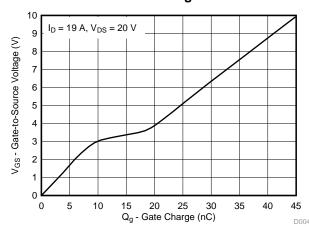




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|------------------|--|---|-----------------------|
|------------------|--|---|-----------------------|

4 Revision History

| Cł | Changes from Original (November 2016) to Revision A | | | | | | |
|----|---|---|--|--|--|--|--|
| • | Changed the charge values in the Dynamic Characteristics section of the <i>Electrical Characteristics</i> table | 3 | | | | | |
| • | Changed Figure 4 in the Typical MOSFET Characteristics section to reflect updated gate charges | 4 | | | | | |

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5 Specifications

5.1 Electrical Characteristics

 $T_A = 25$ °C (unless otherwise stated)

| | PARAMETER | TEST CONDITIONS | MIN T | YP MAX | UNIT |
|---------------------|----------------------------------|--|-------|----------|-------|
| STATIC | CHARACTERISTICS | | ' | | |
| BV _{DSS} | Drain to-source voltage | V _{GS} = 0 V, I _D = 250 μA | 40 | | V |
| I _{DSS} | Drain-to-source leakage current | V _{GS} = 0 V, V _{DS} = 32 V | | 1 | μА |
| I _{GSS} | Gate-to-source leakage current | V _{DS} = 0 V, V _{GS} = 20 V | | 100 | nA |
| V _{GS(th)} | Gate-to-source threshold voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 1.5 | 1.8 2.4 | V |
| D | Drain to course on registence | $V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$ | | 4.1 5.3 | mΩ |
| R _{DS(on)} | Drain-to-source on resistance | V _{GS} = 10 V, I _D = 19 A | | 2.8 3.4 | 11122 |
| g _{fs} | Transconductance | $V_{DS} = 4 \text{ V}, I_{D} = 19 \text{ A}$ | | 89 | S |
| DYNAMI | C CHARACTERISTICS | | | | |
| C _{iss} | Input capacitance | | 33 | 300 4280 | pF |
| C _{oss} | Output capacitance | $V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$ | ; | 333 433 | pF |
| C _{rss} | Reverse transfer capacitance | | | 178 231 | pF |
| R_G | Series gate resistance | | | 0.9 1.8 | Ω |
| Qg | Gate charge total (4.5 V) | | | 23 30 | nC |
| Qg | Gate charge total (10 V) | | | 45 59 | nC |
| Q _{gd} | Gate charge gate-to-drain | V _{DS} = 20 V, I _D = 19 A | | 8.8 | nC |
| Q _{gs} | Gate charge gate-to-source | | | 9.1 | nC |
| Q _{g(th)} | Gate charge at V _{th} | | | 5.8 | nC |
| Q _{oss} | Output charge | V _{DS} = 20 V, V _{GS} = 0 V | | 15 | nC |
| t _{d(on)} | Turnon delay time | | | 6 | ns |
| t _r | Rise time | $V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V},$ | | 12 | ns |
| t _{d(off)} | Turnoff delay time | $I_{DS} = 19 \text{ A}, R_G = 0$ | | 21 | ns |
| t _f | Fall time | | | 4 | ns |
| DIODE C | CHARACTERISTICS | | | | |
| V _{SD} | Diode forward voltage | I _{SD} = 19 A, V _{GS} = 0 V | | 0.8 1.0 | V |
| Q _{rr} | Reverse recovery charge | V _{DS} = 20 V, I _F = 19 A, | | 12 | nC |
| t _{rr} | Reverse recovery time | di/dt = 300 A/μs | | 12 | ns |

5.2 Thermal Information

 $T_A = 25$ °C (unless otherwise stated)

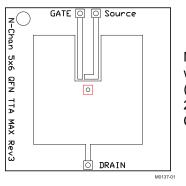
| | THERMAL METRIC | MIN | TYP | MAX | UNIT |
|-----------------|--|-----|-----|-----|------|
| $R_{\theta JC}$ | Junction-to-case thermal resistance ⁽¹⁾ | | | 1.3 | °C/W |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance ⁽¹⁾⁽²⁾ | | | 50 | °C/W |

⁽¹⁾ R_{θJC} is determined with the device mounted on a 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 1.5-in x 1.5-in (3.81-cm x 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.

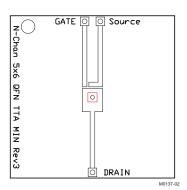
(2) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.

Product Folder Links: CSD18513Q5A





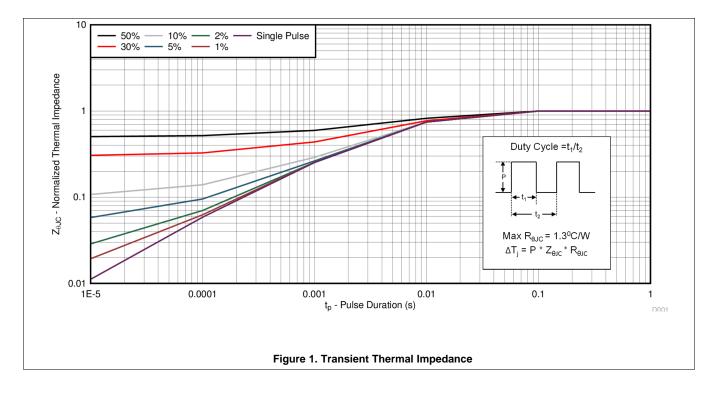
Max $R_{\theta JA} = 50^{\circ} C/W$ when mounted on 1 in² (6.45 cm²) of 2-oz (0.071-mm) thick Cu.



Max $R_{\theta JA} = 125^{\circ} C/W$ when mounted on a minimum pad area of 2-oz (0.071-mm) thick Cu.

5.3 Typical MOSFET Characteristics

 $T_A = 25$ °C (unless otherwise stated)



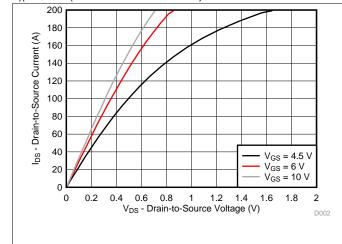
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Typical MOSFET Characteristics (continued)

 $T_A = 25^{\circ}C$ (unless otherwise stated)



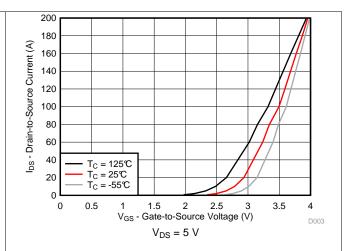
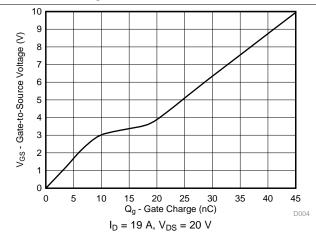


Figure 2. Saturation Characteristics





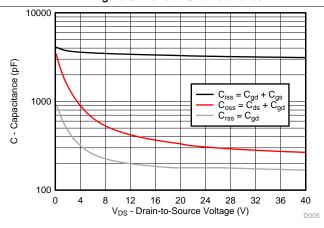


Figure 4. Gate Charge

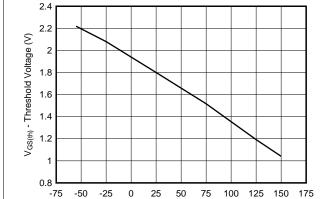


Figure 5. Capacitance

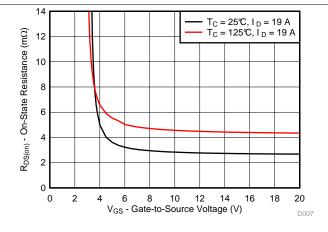


Figure 6. Threshold Voltage vs Temperature

 T_{C} - Case Temperature $(\ensuremath{\mathfrak{C}})$

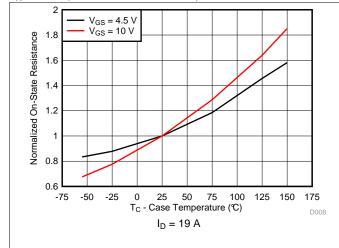
 $I_D = 250 \mu A$

Figure 7. On-State Resistance vs Gate-to-Source Voltage



Typical MOSFET Characteristics (continued)

 $T_A = 25$ °C (unless otherwise stated)



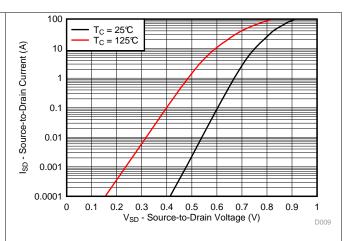
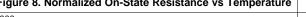


Figure 8. Normalized On-State Resistance vs Temperature



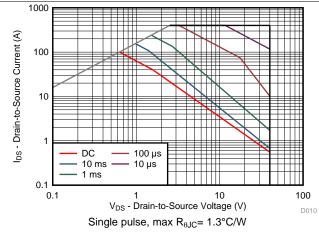


Figure 9. Typical Diode Forward Voltage

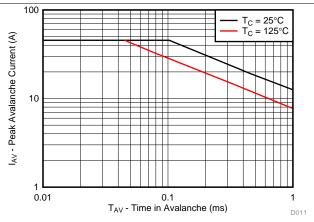
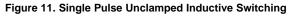


Figure 10. Maximum Safe Operating Area



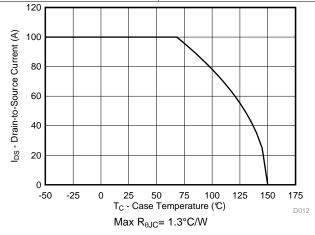


Figure 12. Maximum Drain Current vs Temperature

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6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.3 Trademarks

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6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

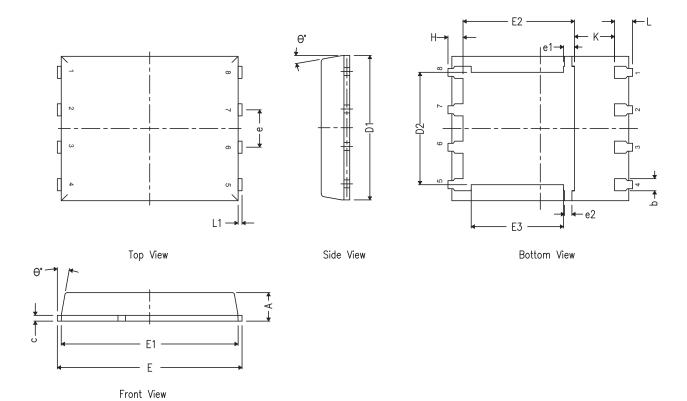
Product Folder Links: CSD18513Q5A



7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q5A Package Dimensions



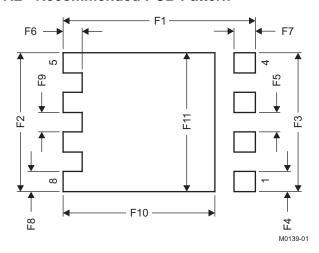
| DIM | | MILLIMETERS | |
|-----|------|-------------|------|
| DIM | MIN | NOM | MAX |
| Α | 0.90 | 1.00 | 1.10 |
| b | 0.33 | 0.41 | 0.51 |
| С | 0.20 | 0.25 | 0.34 |
| D1 | 4.80 | 4.90 | 5.00 |
| D2 | 3.61 | 3.81 | 4.02 |
| E | 5.90 | 6.00 | 6.10 |
| E1 | 5.70 | 5.75 | 5.80 |
| E2 | 3.38 | 3.58 | 3.78 |
| E3 | 3.03 | 3.13 | 3.23 |
| е | 1.17 | 1.27 | 1.37 |
| e1 | 0.27 | 0.37 | 0.47 |
| e2 | 0.15 | 0.25 | 0.35 |
| Н | 0.41 | 0.56 | 0.71 |
| K | 1.10 | _ | _ |
| L | 0.51 | 0.61 | 0.71 |
| L1 | 0.06 | 0.13 | 0.20 |
| θ | 0° | | 12° |

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7.2 Recommended PCB Pattern



| DIM | MILLIME: | TERS | INCH | IES |
|-----|----------|-------|-------|-------|
| DIN | MIN | MAX | MIN | MAX |
| F1 | 6.205 | 6.305 | 0.244 | 0.248 |
| F2 | 4.46 | 4.56 | 0.176 | 0.18 |
| F3 | 4.46 | 4.56 | 0.176 | 0.18 |
| F4 | 0.65 | 0.7 | 0.026 | 0.028 |
| F5 | 0.62 | 0.67 | 0.024 | 0.026 |
| F6 | 0.63 | 0.68 | 0.025 | 0.027 |
| F7 | 0.7 | 8.0 | 0.028 | 0.031 |
| F8 | 0.65 | 0.7 | 0.026 | 0.028 |
| F9 | 0.62 | 0.67 | 0.024 | 0.026 |
| F10 | 4.9 | 5 | 0.193 | 0.197 |
| F11 | 4.46 | 4.56 | 0.176 | 0.18 |

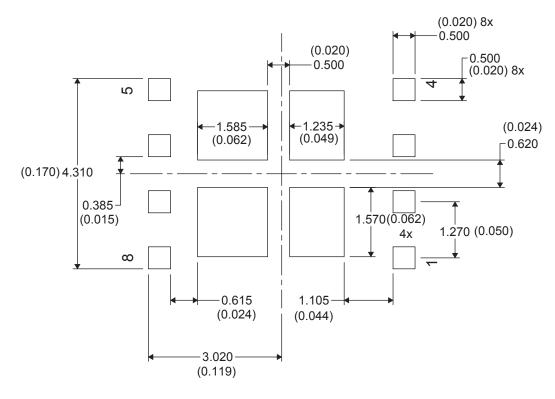
For recommended circuit layout for PCB designs, see *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

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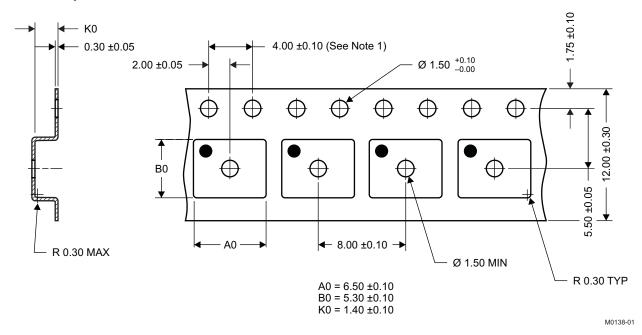
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7.3 Recommended Stencil Opening



7.4 Q5A Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2.
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm.
- 3. Material: black static-dissipative polystyrene.
- 4. All dimensions are in mm (unless otherwise specified).
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.

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www.ti.com 10-Nov-2025

PACKAGING INFORMATION

| Orderable part number | Status | Material type | Package Pins | Package qty Carrier | RoHS | Lead finish/ | MSL rating/ | Op temp (°C) | Part marking |
|-----------------------|--------|---------------|-----------------|-----------------------|-------------|---------------|--------------------|--------------|--------------|
| | (1) | (2) | | | (3) | Ball material | Peak reflow | | (6) |
| | | | | | | (4) | (5) | | |
| CSD18513Q5A | Active | Production | VSONP (DQJ) 8 | 2500 LARGE T&R | ROHS Exempt | SN | Level-1-260C-UNLIM | -55 to 150 | CSD18513 |
| CSD18513Q5A.B | Active | Production | VSONP (DQJ) 8 | 2500 LARGE T&R | ROHS Exempt | SN | Level-1-260C-UNLIM | -55 to 150 | CSD18513 |
| CSD18513Q5AT | Active | Production | VSONP (DQJ) 8 | 250 SMALL T&R | ROHS Exempt | SN | Level-1-260C-UNLIM | -55 to 150 | CSD18513 |
| CSD18513Q5AT.B | Active | Production | VSONP (DQJ) 8 | 250 SMALL T&R | ROHS Exempt | SN | Level-1-260C-UNLIM | -55 to 150 | CSD18513 |

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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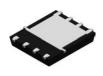
⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

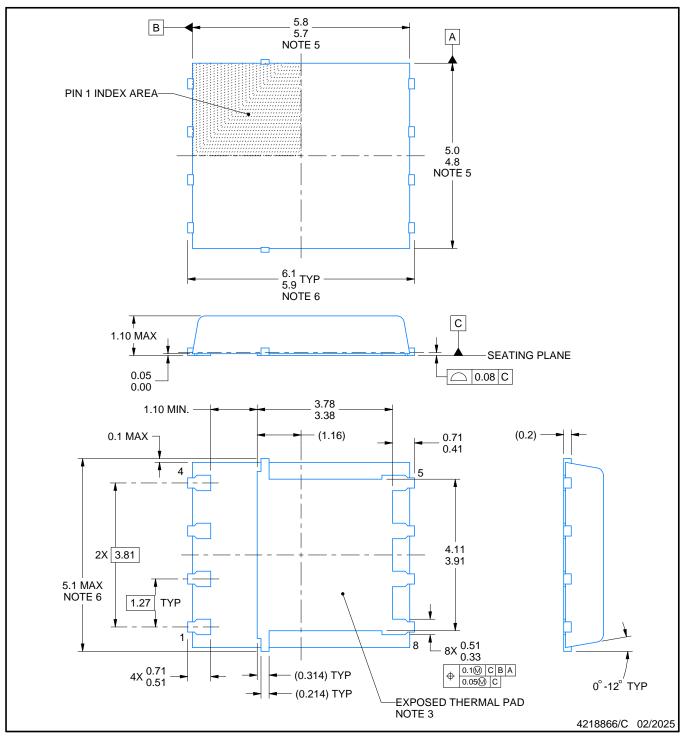
⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PLASTIC SMALL OUTLINE - NO LEAD

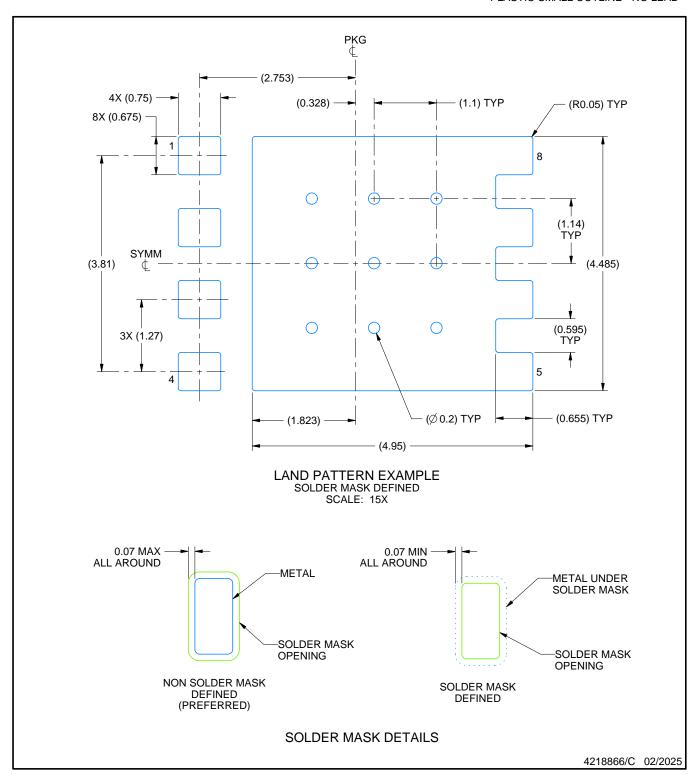


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
- Metalized features are supplier options and may not be on the package.
 These dimensions do not include mold flash protrusions or gate burrs.
- 6. These dimensions include interterminal flash or protrusion. Interterminal flash or protrusion shall not exceed 0.25 mm per side.



PLASTIC SMALL OUTLINE - NO LEAD

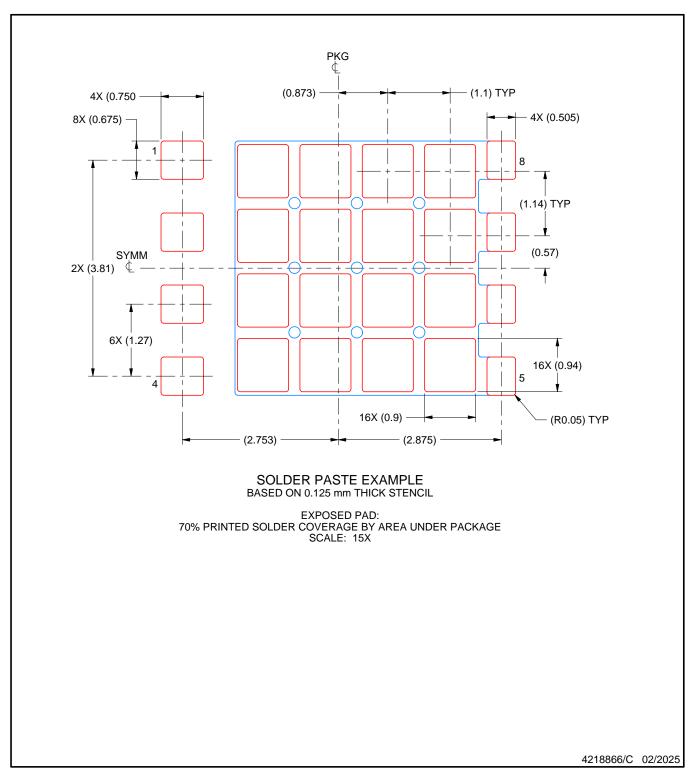


NOTES: (continued)

- 7. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 8. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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